

SANYO	No.3458	2SK1455
		N-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON-state resistance.
- Very high-speed switching.
- Converters.

Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V _{DSS}	900	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current(DC)	I _D	0.2	A
Drain Current(Pulse)	I _{DP}	0.4	A
Allowable Power Dissipation	P _D	30	W
		1.75	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

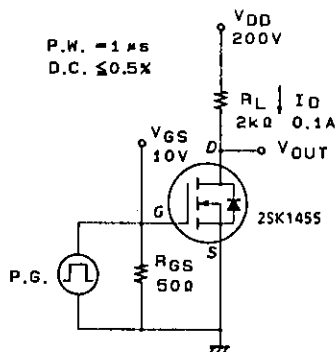
PW ≤ 10μs, duty cycle ≤ 1%
Tc = 25°C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit	
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	900			V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 900V, V _{GS} = 0			1.0	mA	
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±30V, V _{DS} = 0			±100	nA	
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	2.0		3.0	V	
Forward Transfer Admittance	Y _{fs}	V _{DS} = 20V, I _D = 0.1A	0.08	0.15		S	
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = 0.1A, V _{GS} = 10V		50	70	Ω	
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz		45		pF	
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz		25		pF	
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz		10		pF	
Turn-ON Delay Time	t _{d(on)}	I _D = 0.1A, V _{GS} = 10V V _{DD} = 200V, R _{GS} = 50Ω		10		ns	
Rise Time	t _r			15		ns	
Turn-OFF Delay Time	t _{d(off)}				30		ns
Fall Time	t _f				180		ns
Diode Forward Voltage	V _{SD}	I _S = 0.2A, V _{GS} = 0			1.8	V	

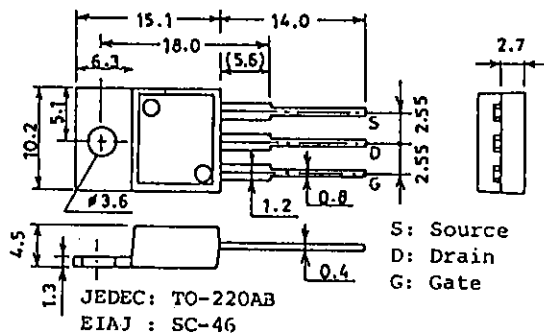
(Note) Be careful in handling the 2SK1455 because it has no protection diode between gate and source.

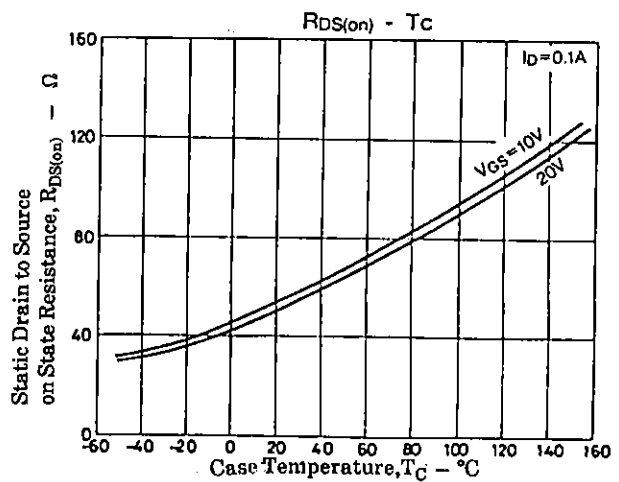
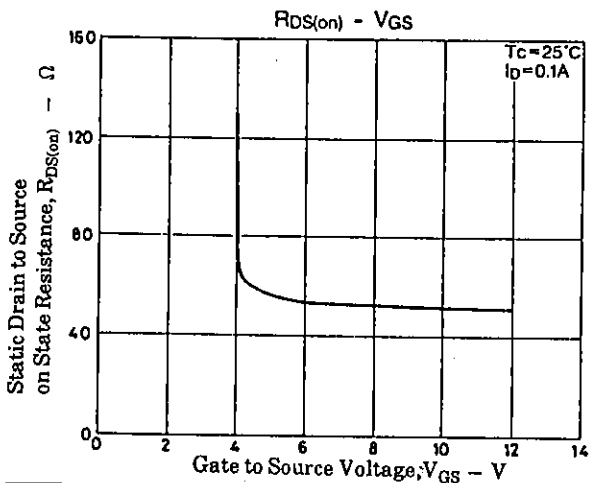
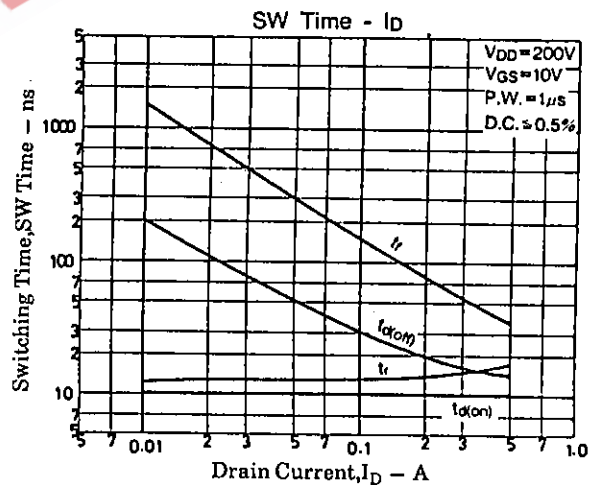
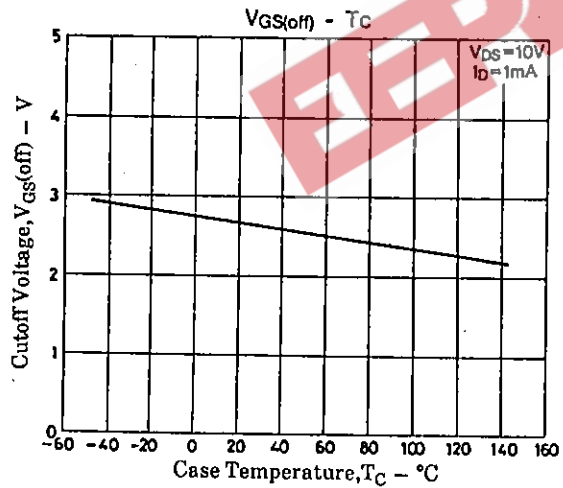
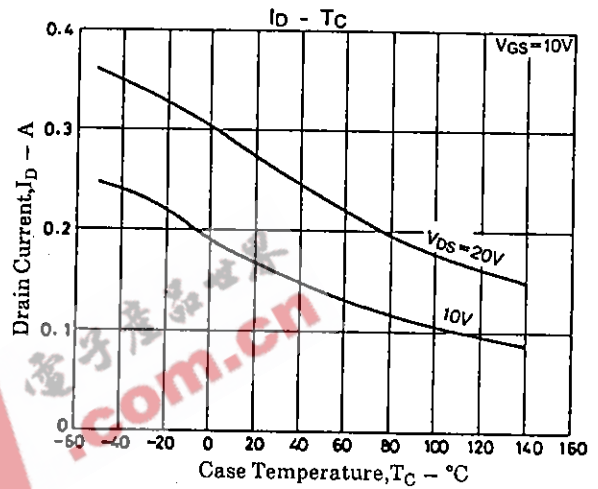
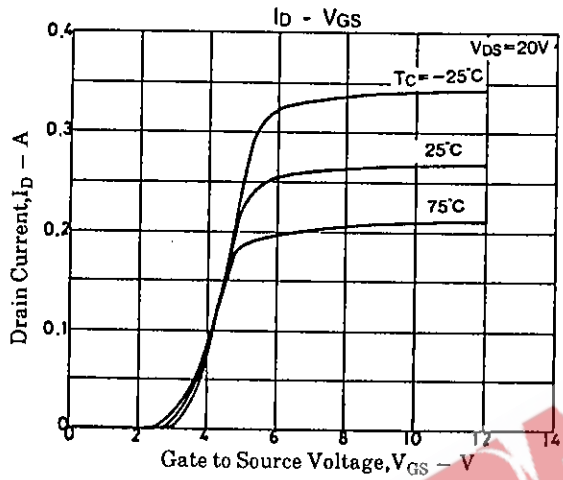
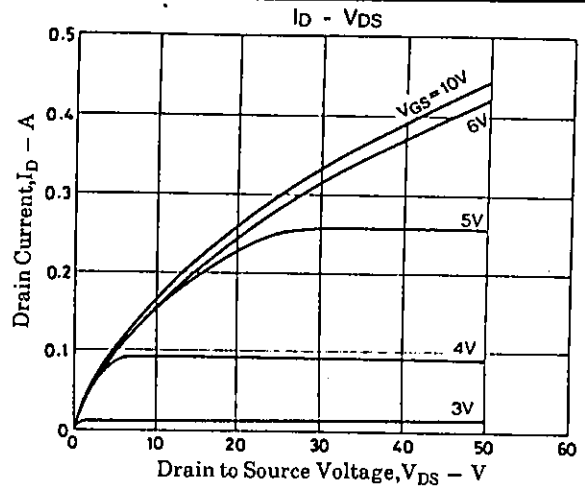
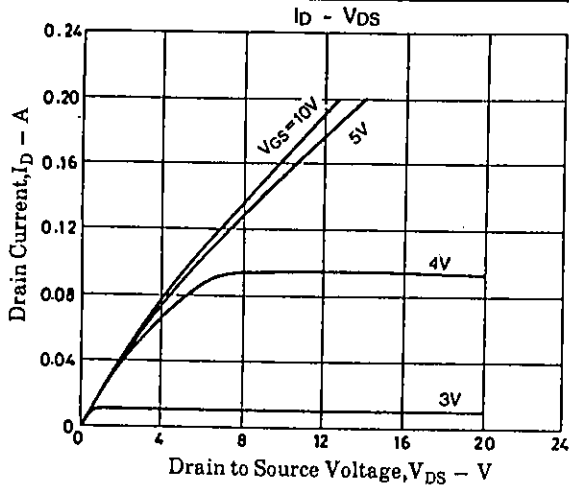
Switching Time Test Circuit

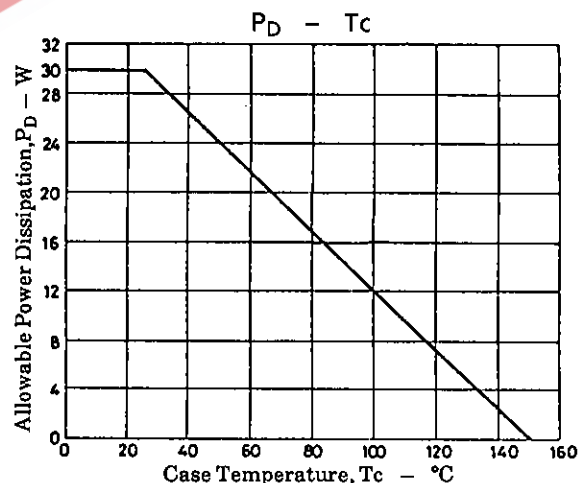
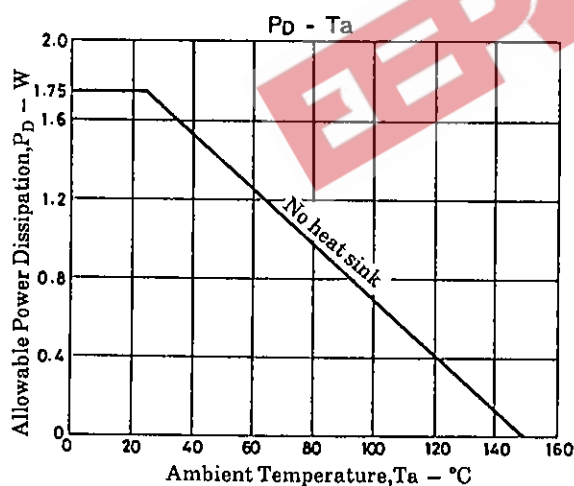
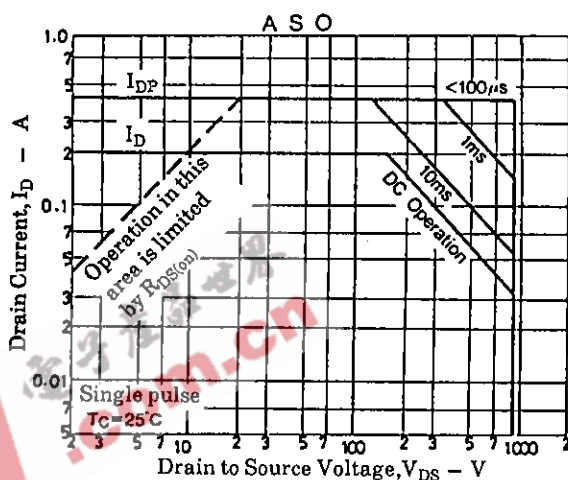
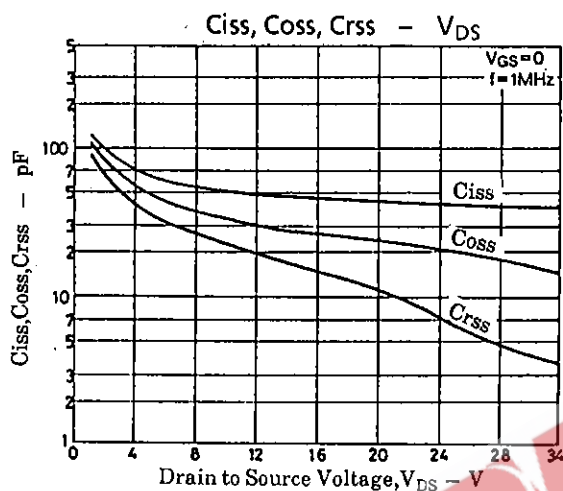
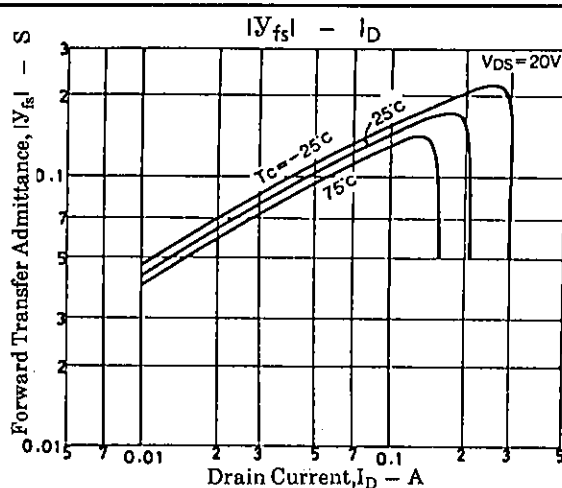
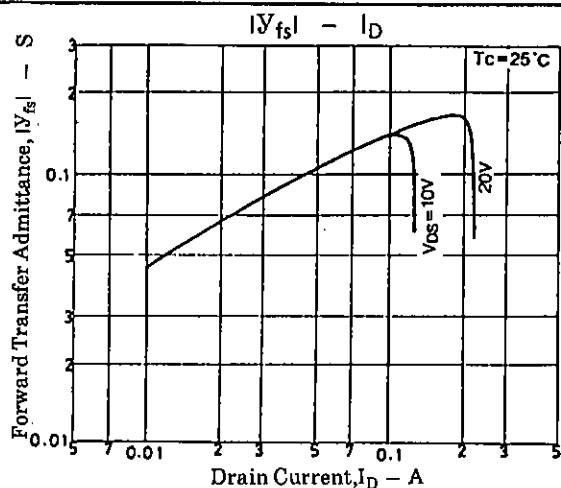


Package Dimensions 2052B

(unit: mm)







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